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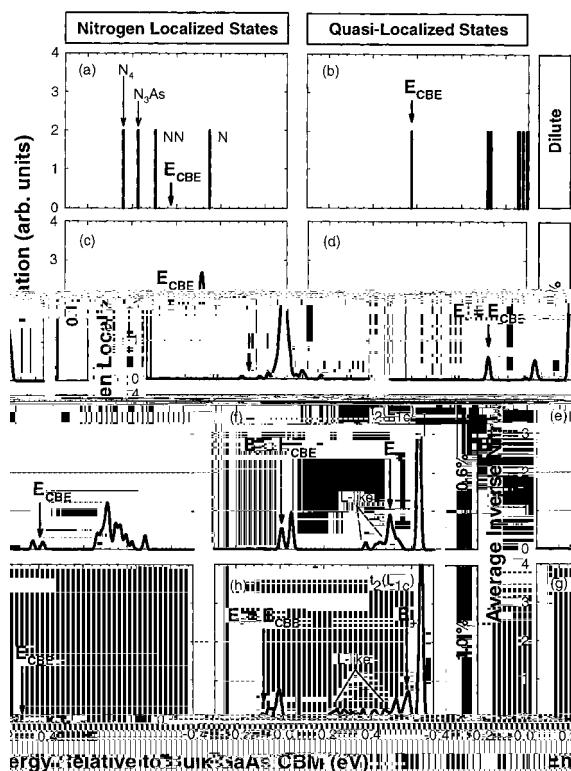
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Abstract : 71.15. ; 71.20. ; 71.55. ; 7.14

1. Introduction : A new class of materials, the so-called "metastable" semiconductors, has been recently discovered [1]. These materials exhibit a band gap that is closed at the Fermi level, but which is partially open at the surface. This is due to the fact that the surface atoms have a different coordination than the bulk atoms. The resulting surface states are localized and have a finite lifetime. This makes it possible to study the properties of the surface without disturbing the bulk. The most common way to study the properties of the surface is by using scanning tunneling microscopy (STM). STM is a non-destructive technique that can be used to image the surface at atomic resolution. It is also possible to use STM to study the electronic properties of the surface. In this paper, we will review the basic principles of STM and discuss some of the recent developments in the field.

where Γ_1 is the first-order Raman scattering intensity, Γ_{11} is the second-order Raman scattering intensity, and Γ_{111} is the third-order Raman scattering intensity. The ratio Γ_{11}/Γ_1 is proportional to the concentration of the N_4 cluster, while the ratio Γ_{111}/Γ_1 is proportional to the concentration of the N_3As cluster. The ratio Γ_{111}/Γ_{11} is proportional to the concentration of the NN cluster. The ratio Γ_{111}/Γ_1 is proportional to the concentration of the N atom. The ratio Γ_{111}/Γ_{11} is proportional to the concentration of the N atom.



$\Gamma = \frac{1}{2}(\Gamma_0 + \Gamma_1)$. A

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